(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization International Bureau



(43) International Publication Date 14 July 2005 (14.07.2005)

PCT

(10) International Publication Number WO 2005/064356 A2

(51) International Patent Classification⁷: 33/09, 15/20, G11C 11/15

G01R 31/30,

(21) International Application Number:

PCT/IB2004/052857

(22) International Filing Date:

20 December 2004 (20.12.2004)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

03104937.2

23 December 2003 (23.12.2003) EI

04105805.8 16 November 2004 (16.11.2004) EP

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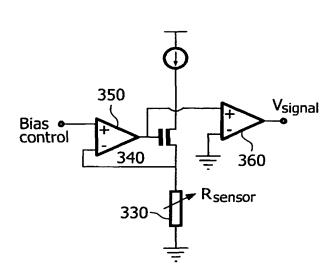
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- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declaration under Rule 4.17:

as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY,

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(54) Title: HIGH SENSITIVITY MAGNETIC BUILT-IN CURRENT SENSOR



(57) Abstract: A sensor for contactlessly detecting currents, has a sensor element having a magnetic tunnel junction (MTJ), and detection circuitry, the sensor element having a resistance which varies with the magnetic field, and the detection circuitry is arranged to detect a tunnel current flowing through the tunnel junction. The sensor element may share an MTJ stack with memory elements. Also it can provide easy integration with next generation CMOS processes, including MRAM technology, be more compact, and use less power. Solutions for increasing sensitivity of the sensor, such as providing a flux concentrator, and for generating higher magnetic fields with a same current, such as forming L-shaped conductor elements, are given. The greater sensitivity enables less post processing to be used, to save power for applications such as mobile devices. Applications include current sensors, built-in current sensors, and IDDQ and IDDT testing, even for next generation CMOS processes.

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TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG)

Published:

 without international search report and to be republished upon receipt of that report

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